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SEMICONDUCTOR THIN FILM (54) MANUFACTURE OF

(57) Abstract:

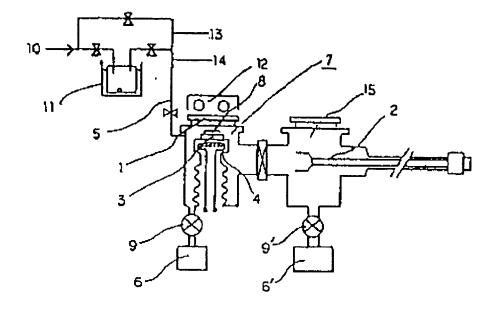
desirably, hydrogen. consisting of fluorosilane, silane or, discomposing a mixture gas single crystalline substrate by photoa single crystalline or amorphous thin film with superior orientation on PURPOSE: To form a semiconductor

crystallineor amorphous single CONSTITUTION: A single or arsine (AsH3) is usable. group compounds, phosphine (PH3) dibolane (B2H6) is usable. As V cleaned with washing or etching is crystalline substrate whose surface is to be added to the mixture gas, usable. As the III group compounds SimH2m+2 (integer of m=1W3) are disilane, trisilane expressed with usable. As the silane, monosilane, nFn(integer of n=1W3) or Si2F6 is former. As the fluorosilane, SiH4flowing ratio of hydrogen to the the flowing ratio of silane to is supplied to the said device, with vaccum discharge. The material gas is heated to 100W400°C under discharge means 6, and the substrate introduction means 5 and a vaccum 3, a substrate heating means 4, a gas window 1, a substrate holding means which has at least a light permiating placed in a thin film forming device 7 fluorosilane being more than twice he fluorosilane being 0.5W50 and the

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